

Microwave Pulse Power Silicon NPN Transistor

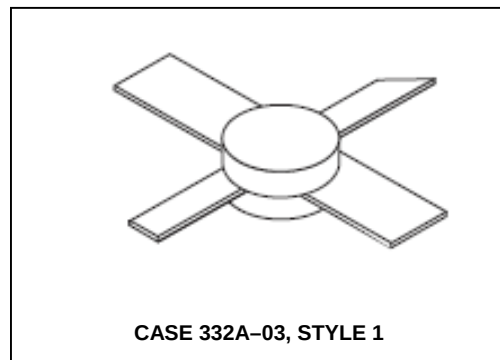
4.0W (peak), 960–1215MHz

M/A-COM Products
Released - Rev. 07.07

Designed for Class B and C common base amplifier applications in short and long pulse TACAN, IFF, DME, and radar transmitters.

- Guaranteed performance @ 1090 MHz, 35 Vdc
Output power = 4.0 W Peak
Minimum gain = 10 dB
- 100% Tested for load mismatch at all phase angles with 10:1 VSWR
- Industry standard package
- Nitride passivated
- Gold metallized, emitter ballasted for long life and resistance to metal migration
- Internal input matching for broadband operation

Product Image



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage	V_{EBO}	3.5	Vdc
Collector Current — Continuous	I_C	250	mA
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ (1) Derate above 25°C	P_D	7.0 40	Watts mW/°C
Storage Temperature Range	T_{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (2)	$R_{\theta JC}$	25	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 5.0$ mA, $I_B = 0$)	$V_{(BR)CEO}$	20	—	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 5.0$ mA, $V_{BE} = 0$)	$V_{(BR)CES}$	50	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 5.0$ mA, $I_E = 0$)	$V_{(BR)CBO}$	50	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 1.0$ mA, $I_C = 0$)	$V_{(BR)EBO}$	3.5	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 35$ Vdc, $I_E = 0$)	I_{CBO}	—	—	0.5	mA

ON CHARACTERISTICS

DC Current Gain ($I_C = 75$ mA, $V_{CE} = 5.0$ Vdc)	h_{FE}	10	—	100	—
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NOTES:

(continued)

- These devices are designed for RF operation. The total device dissipation rating applies only when the device is operated as RF amplifiers.
- Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.

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ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted)

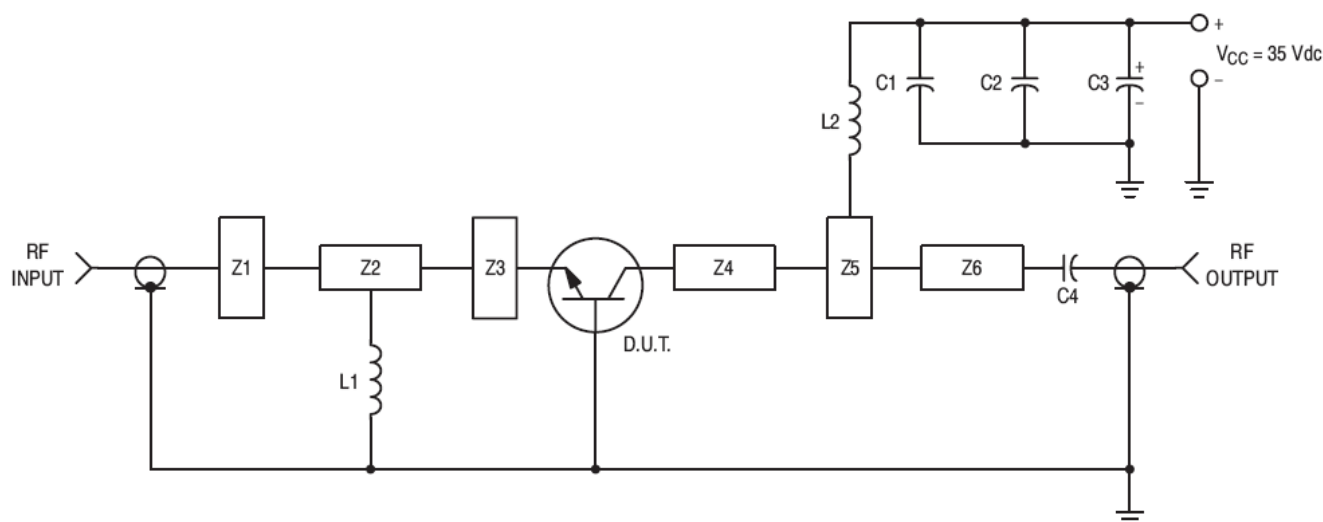
Characteristic	Symbol	Min	Typ	Max	Unit
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DYNAMIC CHARACTERISTICS

Output Capacitance ($V_{CB} = 35\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{ob}	—	3.3	5.0	pF
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FUNCTIONAL TESTS (Pulse Width = $10\text{ }\mu\text{s}$, Duty Cycle = 1.0%)

Common-Base Amplifier Power Gain ($V_{CC} = 35\text{ Vdc}$, $P_{out} = 4.0\text{ W pk}$, $f = 1090\text{ MHz}$)	G_{PB}	10	11	—	dB
Collector Efficiency ($V_{CC} = 35\text{ Vdc}$, $P_{out} = 4.0\text{ W pk}$, $f = 1090\text{ MHz}$)	η	40	45	—	dB
Load Mismatch ($V_{CC} = 35\text{ Vdc}$, $P_{out} = 4.0\text{ W pk}$, $f = 1090\text{ MHz}$, VSWR = 10:1 All Phase Angles)	ψ	No Degradation in Power Output			



C1 — $0.1\text{ }\mu\text{F}$
C2, C4 — 220 pF Chip Capacitor
C3 — $20\text{ }\mu\text{F}$, 50 V Electrolytic
L1, L2 — 3 Turns #18 AWG, $1/8''$ ID
Z1–Z6 Distributed Microstrip Elements, See Photomaster
Board Material — $0.031''$ Thick Glass Teflon

Figure 1. 1090 MHz Test Circuit

TYPICAL CHARACTERISTICS

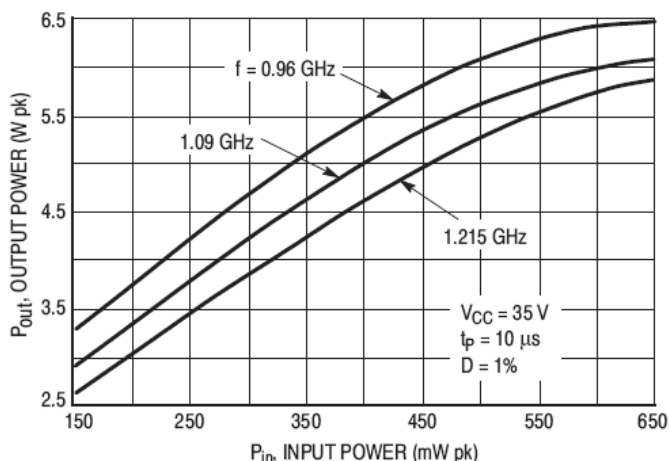


Figure 2. Output Power versus Input Power

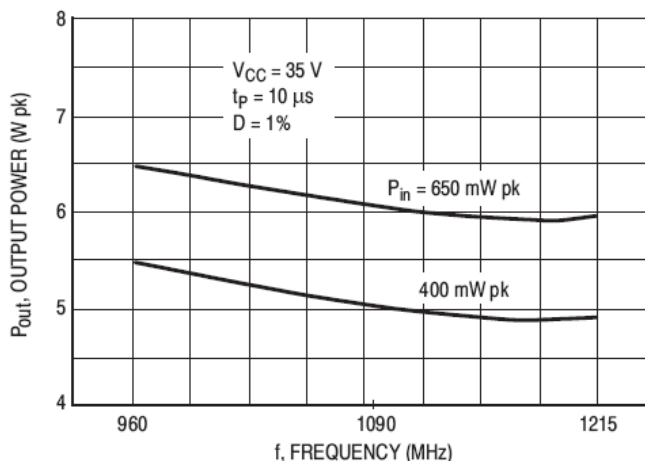


Figure 3. Output Power versus Frequency

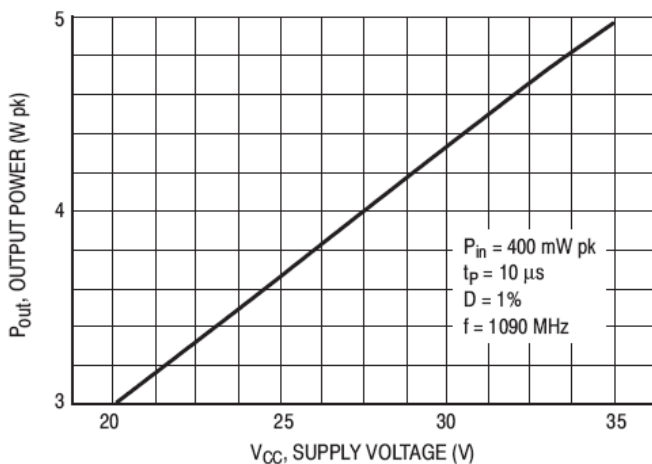


Figure 4. Output Power versus Supply Voltage

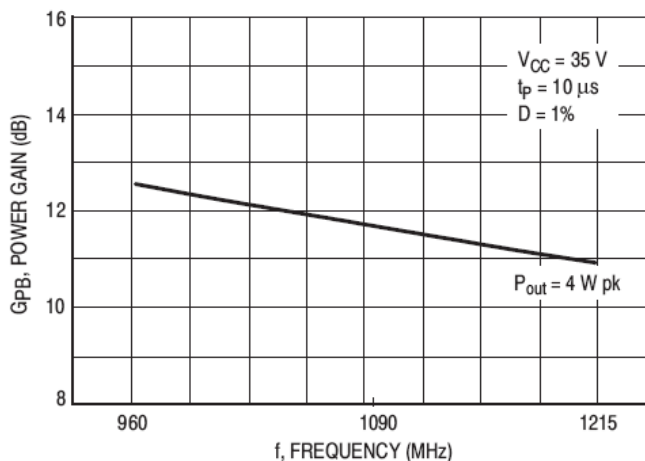


Figure 5. Power Gain versus Frequency

TYPICAL CHARACTERISTICS

$P_{out} = 4 \text{ W pk}$
 $V_{CC} = 35 \text{ V}$
 $t_p = 1 \text{ ms}$
 $D = 10\%$
 $f = 1090 \text{ MHz}$

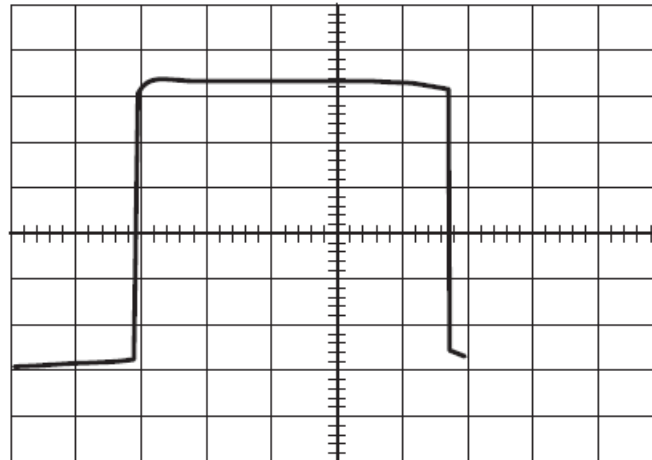


Figure 7. Typical Long Pulse Performance

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PACKAGE DIMENSIONS

